ECE 137 A Mid-Term Exam

Thursday February 5, 2015

Do not open exam until instructed to.

Closed book: Crib sheet and 1 page personal notes permitted

There are 3 problems on this exam, and you have 75 minutes.

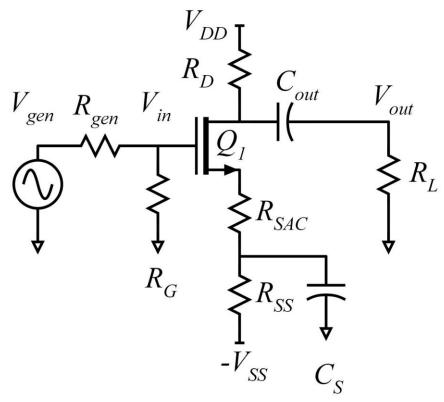
Use any and all reasonable approximations (5% accuracy is fine.), AFTER STATING and approximately Justifying them.

Name:		
1 1WIIIC.		

Part	Points	Points	Part	Points	Points
	Received	Possible		Received	Possible
1a		10	2f		15
1b		5	3a		8
1c		5	3b		8
1d		10	3c		4
1e		15			
2a		10			
2b		5			
2c		5			
2d		10			
2e		5			
TOTAL					100

Problem 1, 30 points

You will be working on the circuit below:



The transistor has

$$L_g$$
 =45nm, μ =400 cm²/V-s, $\varepsilon_{r,ox}$ =3.8, T_{ox} =1nm, v_{sat} =10⁷cm/s, V_{th} = 0.284V, $1/\lambda$ = 10V,

From which we calculate:

$$c_{ox}v_{sat}$$
 = 3.36 mA/V/ μ m, μc_{ox} / $2L_g$ = 15 mA/V²/ μ m, $\Delta V = L_g v_{th}$ / μ = 0.113V,

The supplies are +1V and -1V

You are to bias the transistor at 2mA drain current,

with 0.6V DC drain voltage, and with -0.45 V DC source voltage.

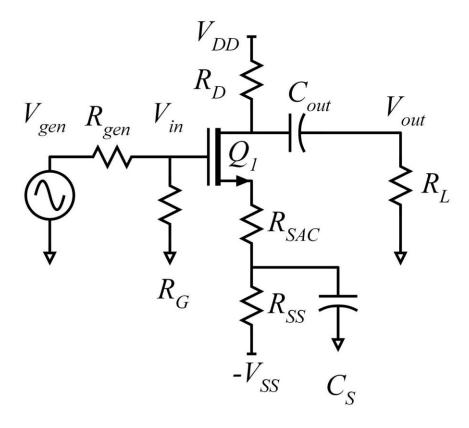
$$R_{SAC} = 20 \Omega$$
, $R_G = 1 \text{ M}\Omega$, $R_{gen} = 75 \text{ k}\Omega$, $R_L = 10 \text{ k}\Omega$

 C_s and C_{out} are very large (AC short-circuit)

Part a, 10 points			
DC bias.			
Use this approximation: Igno	ore (i.e. set to zero) the l	FET λ parameter in the Do	C bias
calculation.			
Find the following:			
FET gate width Wg=	Rss=	RD=	

Part b, 5 points

DC bias



On the circuit diagram above, label the DC voltages at \pmb{ALL} nodes and the DC currents through \pmb{ALL} resistors

Part c, 5 points		
Using the actua	al (nonzero) FET	λ parameter, find the FET small signal parameters
am-	Pde-	

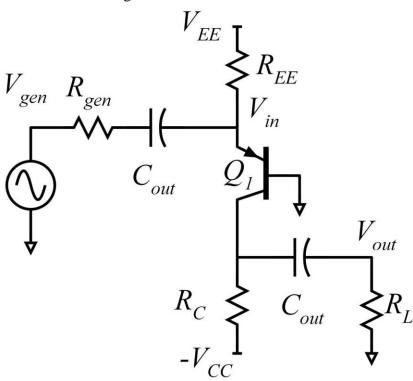
Part d, 10 points.	
Find the small signal voltage gain resistance.	Vout/Vin and the amplifier small-signal input

Vout/Vin=____

Rin, amplfier = _____

Problem 2, 50 points

You will be working on the circuit below:



Q1: $\beta = 100$, $V_A = \text{infinity V}$

The supplies are +5V and -5 V.

You will bias the transistor with 2mA collector current.

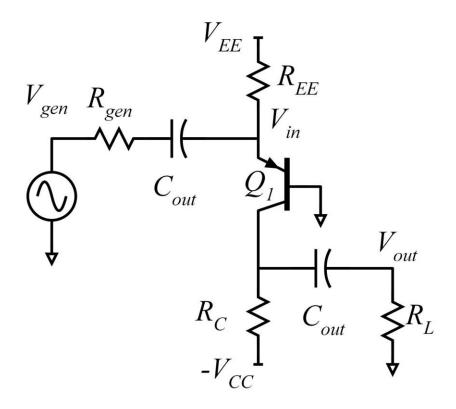
The DC collector bias voltage is -2.5V.

 $R_L \, \text{is} \, 10 \, \text{k}\Omega \, , \; R_{gen} \, \, \text{is} \, 100 \, \, \Omega$

Part a, 10 points	
DC bias.	
Find the following:	
$R_{FF} = $	$R_C =$

Part b, 5 points

DC bias



On the circuit diagram above, label the DC voltages at **ALL nodes** and the DC currents through **ALL resistors**

Part c, 5 points			
Find the small s	ignal parameters of Q	1.	
am-	\mathbf{p}_{co}	Rhe-	

Part	d,	10	points.

Find the small si	ignal voltage gain	(Vout/Vin) of Q1	and the amplifier	small-signal input
resistance.				

Vout/Vin=____

Rin,amp=____

Part e, 5 points
Find (Vin/Vgen) and (Vout/Vgen)
(Vin/Vgen) =
(Vout/Vgen) =

Part f, 15 points

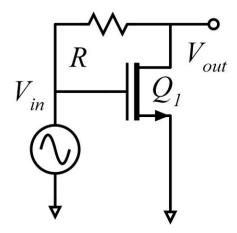
Now you must find the maximum	ı signal swings.	Find the	output voltage	due	to
saturation and cutoff in Q2. Give	the sign (+ or -) in your	answers below.		

Cutoff of Q1; Maximum Δ Vout resulting = _____

Saturation of Q1; Maximum Δ Vout resulting = _____

Problem 3, 20 points

nodal analysis



You will be working on the circuit to the left.

Ignore DC bias analysis. You don't need it.

Transistor 1 has transconductance gm1.

The drain-source resistance Rds of the transistor is infinity (so you don't need to draw it!)

Part a, 8 points

Draw the small-signal equivalent circuit

Part b, 8 points
Find, by nodal analysis, a small-signal expression for Vout/Vin.
Vout/Vin=

Part c, 4 points

gm1= 1 mS , R=3kOhm Give a numerical value for Vout/Vin.

Vout/Vin=____